		2N6052 2N6059					
COMPLEMENTARY SILICON DARLINGTON POWER TRANSISTORS							
Central							
TO-3 CASE							

Γ



www.centralsemi.com

DESCRIPTION:

Т

The CENTRAL SEMICONDUCTOR 2N6050, 2N6057 series types are complementary silicon Darlington power transistors, manufactured by the epitaxial base process, designed for high gain amplifier and switching applications.

MARKING: FULL PART NUMBER

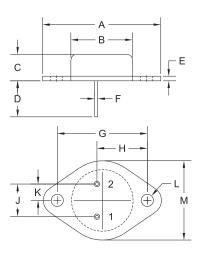
MAXIMUM RATINGS: (T _C =25°C) Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Continuous Collector Current Peak Collector Current Continuous Base Current Power Dissipation Operating and Storage Junction Temperature Thermal Resistance		SYMBOL VCBO VCEO IC ICM IB PD TJ, Tstg Θ JC	2N6050 <u>2N6057</u> 60 60	2N6051 <u>2N6058</u> 80 5.0 12 20 0.2 150 -65 to +200 1.17	2N6052 <u>2N6059</u> 100 100	UNITS V V A A A W °C °C/W
ELECTRICAL SYMBOL I _{CEV} I _{CEV}	- CHARACTERISTICS: $(T_C=25^{\circ}C \text{ un})$ TEST CONDITIONS $V_{CE}=Rated V_{CEO}, V_{EB}=1.5V$ $V_{CF}=Rated V_{CEO}, V_{FB}=1.5V, T_{C}=1.5V$	MIN	e noted)	MAX 0.5 5.0		UNITS mA mA
ICEO	V _{CE} =½Rated V _{CEO}	100 0		1.0		mA
I _{EBO}	V _{EB} =5.0V			2.0		mA
BVCEO	I _C =100mA, (2N6050, 2N6057)	60				V
BVCEO	I _C =100mA, (2N6051, 2N6058)	80				V
BVCEO	I _C =100mA, (2N6052, 2N6059)	100				V
V _{CE(SAT)}	I _C =6.0A, I _B =24mA			2.0		V
V _{CE(SAT)}	I _C =12A, I _B =120mA			3.0		V
V _{BE(SAT)}	I _C =12A, I _B =120mA			4.0		V
V _{BE(ON)}	V _{CE} =3.0V, I _C =6.0A			2.8		V
h _{FE}	V _{CE} =3.0V, I _C =6.0A	750		18K		
h _{FE}	V _{CE} =3.0V, I _C =12A	100				
h _{fe}	V _{CE} =3.0V, I _C =5.0A, f=1.0kHz	300				
fT	V _{CE} =3.0V, I _C =5.0A, f=1.0MHz	4.0				MHz
Cob	V _{CB} =10V, I _E =0, f=100kHz (PNP typ			500		pF
Cob	V_{CB} =10V, I _E =0, f=100kHz (NPN typ	bes)		300		pF

R1 (18-September 2012)



2N6050 2N6051 2N6052 PNP 2N6057 2N6058 2N6059 NPN

COMPLEMENTARY SILICON DARLINGTON POWER TRANSISTORS



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
А	1.516	1.573	38.50	39.96			
B (DIA)	0.748	0.875	19.00	22.23			
С	0.250	0.450	6.35	11.43			
D	0.433	0.516	11.00	13.10			
E	0.054	0.065	1.38	1.65			
F	0.035	0.045	0.90	1.15			
G	1.177	1.197	29.90	30.40			
Н	0.650	0.681	16.50	17.30			
J	0.420	0.440	10.67	11.18			
K	0.205	0.225	5.21	5.72			
L (DIA)	0.151	0.172	3.84	4.36			
М	0.984	1.050	25.00	26.67			
TO-3 (REV: R2)							

R2

TO-3 CASE - MECHANICAL OUTLINE

LEAD CODE: 1) Base 2) Emitter Case) Collector

> MARKING: FULL PART NUMBER

www.centralsemi.com

R1 (18-September 2012)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp. 145 Adams Avenue Hauppauge, NY 11788 USA Main Tel: (631) 435-1110 Main Fax: (631) 435-1824 Support Team Fax: (631) 435-3388 www.centralsemi.com

Worldwide Field Representatives: www.centralsemi.com/wwreps

Worldwide Distributors: www.centralsemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: <u>www.centralsemi.com/terms</u>

www.centralsemi.com

